| $\mathrm{V}_{\text {Dss }}$ | 650 V |
| :---: | :---: |
| $\mathrm{R}_{\mathrm{DS} \text { (on) }}$ (Typ.) | $30 \mathrm{~m} \Omega$ |
| $\mathrm{I}_{\mathrm{D}}{ }^{\text {4 }}$ | 70 A |
| $\mathrm{P}_{\mathrm{D}}$ | 262 W |

-Outline


- Inner circuit


## -Features

1) Qualified to AEC-Q101
2) Low on-resistance
3) Fast switching speed
4) Fast reverse recovery
5) Easy to parallel
6) Simple to drive
7) Pb-free lead plating ; RoHS compliant

## - Application

- Automobile
- Switch mode power supplies


Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.
-Packaging specifications

| Type | Packing | Tube |
| :--- | :--- | :---: |
|  | Reel size $(\mathrm{mm})$ | - |
|  | Tape width $(\mathrm{mm})$ | - |
|  | Basic ordering unit $(\mathrm{pcs})$ | 30 |
|  | Taping code | C 15 |
|  | Marking | SCT3030AR |

- Absolute maximum ratings $\left(\mathrm{T}_{\mathrm{vj}}=25^{\circ} \mathrm{C}\right.$ unless otherwise specified)

| Parameter |  | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Drain - Source Voltage |  | $\mathrm{V}_{\text {DSS }}$ | 650 | V |
| Continuous Drain current | $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}$ | $\mathrm{I}_{\mathrm{D}}{ }^{1}$ | 70 | A |
|  | $\mathrm{T}_{\mathrm{c}}=100^{\circ} \mathrm{C}$ | $\mathrm{I}_{\mathrm{D}}{ }^{1}$ | 49 | A |
| Pulsed Drain current ( $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}$ ) |  | $\mathrm{I}_{\mathrm{p} \text { pulse }}{ }^{*}{ }^{\text {2 }}$ | 175 | A |
| Gate - Source voltage (DC) |  | $\mathrm{V}_{\text {GSS }}$ | -4 to +22 | V |
| Gate - Source surge voltage ( $\mathrm{t}_{\text {surge }}<300 \mathrm{~ns}$ ) |  | $\mathrm{V}_{\text {GSS_surge }}{ }^{\text {3 }}$ | -4 to +26 | V |
| Recommended drive voltage |  | $\mathrm{V}_{\mathrm{GS} \text { _op }}{ }^{*}$ | $0 /+18$ | V |
| Virtual Junction temperature |  | $\mathrm{T}_{\mathrm{vj}}$ | 175 | ${ }^{\circ} \mathrm{C}$ |
| Range of storage temperature |  | $\mathrm{T}_{\text {stg }}$ | -55 to +175 | ${ }^{\circ} \mathrm{C}$ |

$\bullet$ Electrical characteristics $\left(\mathrm{T}_{\mathrm{vj}}=25^{\circ} \mathrm{C}\right.$ unless otherwise specified)

| Parameter | Symbol | Conditions | Values |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Typ. | Max. |  |
| Drain - Source breakdown voltage | $\mathrm{V}_{\text {(BR) } \mathrm{DSS}}$ | $\begin{aligned} & V_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1 \mathrm{~mA} \\ & \mathrm{~T}_{\mathrm{vj}}=25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{vj}}=-55^{\circ} \mathrm{C} \end{aligned}$ | $\begin{aligned} & 650 \\ & 650 \end{aligned}$ |  | - | V |
| Zero Gate voltage <br> Drain current | I DSs | $\begin{aligned} & V_{G S}=0 \mathrm{~V}, V_{D S}=650 \mathrm{~V} \\ & T_{\mathrm{vj}}=25^{\circ} \mathrm{C} \\ & T_{\mathrm{vj}}=150^{\circ} \mathrm{C} \end{aligned}$ | - | $\begin{aligned} & 1 \\ & 2 \end{aligned}$ | 10 | $\mu \mathrm{A}$ |
| Gate - Source leakage current | $\mathrm{I}_{\text {GSS }+}$ | $\mathrm{V}_{\mathrm{GS}}=+22 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ | - | - | 100 | nA |
| Gate - Source leakage current | $\mathrm{I}_{\text {GSS }}$ | $\mathrm{V}_{\mathrm{GS}}=-4 \mathrm{~V}, \quad \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ | - | - | -100 | nA |
| Gate threshold voltage | $\mathrm{V}_{\mathrm{GS}}(\mathrm{th})$ | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=13.3 \mathrm{~mA}$ | 2.7 | - | 5.6 | V |
| Static Drain - Source on - state resistance | $\mathrm{R}_{\mathrm{DS} \text { (on) }}{ }^{* 5}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{GS}}=18 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=27 \mathrm{~A} \\ & \mathrm{~T}_{\mathrm{Vj}}=25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{Vj}}=150^{\circ} \mathrm{C} \end{aligned}$ | - | $\begin{aligned} & 30 \\ & 43 \end{aligned}$ | $39$ | $\mathrm{m} \Omega$ |
| Gate input resistance | $\mathrm{R}_{\mathrm{G}}$ | $\mathrm{f}=1 \mathrm{MHz}$, open drain | - | 7 | - | $\Omega$ |

- Thermal resistance

| Parameter | Symbol | Values |  |  | Unit |
| :--- | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Typ. | Max. |  |
| Thermal resistance, junction - case | $\mathrm{R}_{\text {thJc }}$ | - | 0.44 | 0.57 | K/W |

-Typical Transient Thermal Characteristics

| Symbol | Value | Unit | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\mathrm{th} 1}$ | $2.56 \times 10^{-2}$ | K/W | $\mathrm{C}_{\text {th1 }}$ | $1.39 \times 10^{-3}$ | Ws/K |
| $\mathrm{R}_{\mathrm{th} 2}$ | $1.95 \times 10^{-1}$ |  | $\mathrm{C}_{\text {th2 }}$ | $1.00 \times 10^{-2}$ |  |
| $\mathrm{R}_{\text {th3 }}$ | $2.20 \times 10^{-1}$ |  | $\mathrm{C}_{\text {th3 }}$ | $3.57 \times 10^{-2}$ |  |


-Electrical characteristics $\left(\mathrm{T}_{\mathrm{vj}}=25^{\circ} \mathrm{C}\right.$ unless otherwise specified)

| Parameter | Symbol | Conditions | Values |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Typ. | Max. |  |
| Transconductance | $\mathrm{g}_{\text {ts }}{ }^{\text {5 }}$ | $V_{D S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=27 \mathrm{~A}$ | - | 9.4 | - | S |
| Input capacitance | $\mathrm{C}_{\text {iss }}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{DS}}=500 \mathrm{~V} \\ & \mathrm{f}=1 \mathrm{MHz} \end{aligned}$ | - | 1526 | - | pF |
| Output capacitance | $\mathrm{C}_{\text {oss }}$ |  | - | 89 | - |  |
| Reverse transfer capacitance | $\mathrm{C}_{\text {rss }}$ |  | - | 42 | - |  |
| Effective output capacitance, energy related | $\mathrm{C}_{\text {o(er) }}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V} \text { to } 300 \mathrm{~V} \end{aligned}$ | - | 230 | - | pF |
| Total Gate charge | $Q_{g}{ }^{\text {5 }}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{DS}}=300 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{D}}=27 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{GS}}=18 \mathrm{~V} \end{aligned}$ <br> See Fig. 1-1. | - | 104 | - | nC |
| Gate - Source charge | $\mathrm{Q}_{\mathrm{gs}}{ }^{* 5}$ |  | - | 19 | - |  |
| Gate - Drain charge | $\mathrm{Q}_{\mathrm{gd}}{ }^{* 5}$ |  | - | 55 | - |  |
| Turn - on delay time | $\mathrm{t}_{\mathrm{d}(\mathrm{O})}{ }^{* 5}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{DS}}=400 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{D}}=40 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V} /+18 \mathrm{~V} \\ & \mathrm{R}_{\mathrm{G}}=0 \Omega, \mathrm{~L}=750 \mu \mathrm{H} \\ & \mathrm{~L}_{\sigma}=50 \mathrm{nH}, \mathrm{C}_{\sigma}=10 \mathrm{pF} \end{aligned}$ <br> See Fig. 2-1, 2-2, 2-3. <br> $\mathrm{E}_{\text {on }}$ includes diode reverse recovery. | - | 6 | - | ns |
| Rise time | $\mathrm{tr}^{*}{ }^{5}$ |  | - | 26 | - |  |
| Turn - off delay time | $\mathrm{t}_{\mathrm{d} \text { (ffi) }}{ }^{* 5}$ |  | - | 25 | - |  |
| Fall time | $\mathrm{t}_{\mathrm{f}}{ }^{5}$ |  | - | 25 | - |  |
| Turn - on switching loss | $\mathrm{E}_{\text {on }}{ }^{* 5}$ |  | - | 203 | - | $\mu \mathrm{J}$ |
| Turn - off switching loss | $\mathrm{E}_{\text {off }}{ }^{*}$ |  | - | 175 | - |  |

-Body diode electrical characteristics (Source-Drain) ( $\mathrm{T}_{\mathrm{vj}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Values |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Typ. | Max. |  |
| Body diode continuous, forward current | $\mathrm{I}^{*}{ }^{*}$ | $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}$ |  |  | 70 | A |
| Body diode direct current, pulsed | $1 \mathrm{ISM}^{*}{ }^{2}$ |  | - | - | 175 | A |
| Forward voltage | $\mathrm{V}_{\text {SD }}{ }^{* 5}$ | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{S}}=27 \mathrm{~A}$ |  | 3.2 | - | V |
| Reverse recovery time | $\mathrm{trr}^{*}{ }^{5}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=27 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{R}}=400 \mathrm{~V} \\ & \mathrm{di} / \mathrm{dt}=2500 \mathrm{~A} / \mu \mathrm{s} \\ & \mathrm{~L}_{\sigma}=50 \mathrm{nH}, \mathrm{C}_{\sigma}=10 \mathrm{pF} \end{aligned}$ <br> See Fig. 3-1, 3-2. | - | 28 | - | ns |
| Reverse recovery charge | $\mathrm{Q}_{\text {rr }}{ }^{5}$ |  | - | 702 | - | nC |
| Peak reverse recovery current | $\mathrm{Irm}^{*}{ }^{\text { }}$ |  | - | 40 | - | A |

*1 Limited by maximum $\mathrm{T}_{\mathrm{vj}}$ and for Max. $\mathrm{R}_{\mathrm{th} \mathrm{Jc}}$.
*2 PW $\leq 10 \mu \mathrm{~s}$, Duty cycle $\leq 1 \%$
*3 Example of acceptable $\mathrm{V}_{\mathrm{GS}}$ waveform


Please note especially when using driver source that $\mathrm{V}_{\text {GSS_surge }}$ must be in the range of absolute maximum rating.
*4 Please be advised not to use SiC-MOSFETs with $\mathrm{V}_{\mathrm{GS}}$ below 13 V as doing so may cause thermal runaway.
*5 Pulsed

## - Electrical characteristic curves

Fig. 1 Power Dissipation Derating Curve


Fig. 3 Typical Transient Thermal Impedance vs. Pulse Width


Fig. 2 Maximum Safe Operating Area


## - Electrical characteristic curves

Fig. 4 Typical Output Characteristics(I)


Fig. 5 Typical Output Characteristics(II)


Fig. $6 \mathrm{~T}_{\mathrm{vj}}=25^{\circ} \mathrm{C}$ 3rd Quadrant Characteristics


## - Electrical characteristic curves

Fig. $7 \mathrm{~T}_{\mathrm{vj}}=150^{\circ} \mathrm{C}$ Typical Output Characteristics(I)


Fig. $9 \mathrm{~T}_{\mathrm{vj}}=150^{\circ} \mathrm{C}$ 3rd Quadrant Characteristics


Fig. $8 \mathrm{~T}_{\mathrm{vj}}=150^{\circ} \mathrm{C}$ Typical Output Characteristics(II)


Fig. 10 Body Diode Forward Voltage vs. Gate - Source Voltage


## - Electrical characteristic curves

Fig. 11 Typical Transfer Characteristics (I)


Fig. 13 Gate Threshold Voltage vs. Virtual Junction Temperature


Fig. 12 Typical Transfer Characteristics (II)


Fig. 14 Transconductance vs. Drain Current


## - Electrical characteristic curves

Fig. 15 Static Drain - Source On - State
Resistance vs. Gate - Source Voltage


Fig. 17 Static Drain - Source On - State Resistance vs. Drain Current


Fig. 16 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature


Fig. 18 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction Temperature


## - Electrical characteristic curves

Fig. 19 Typical Capacitance
vs. Drain - Source Voltage


Fig. 21 Dynamic Input Characteristics


Fig. $20 \mathrm{C}_{\text {oss }}$ Stored Energy


- Electrical characteristic curves

Fig. 22 Typical Switching Time
vs. External Gate Resistance


Fig. 24 Typical Switching Loss
vs. Drain Current


Fig. 23 Typical Switching Loss
vs. Drain - Source Voltage


Fig. 25 Typical Switching Loss
vs. External Gate Resistance


## $\bullet$ Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit


Fig.2-1 Switching Characteristics Measurement Circuit


Fig.2-2 Waveforms for Switching Time


Fig.2-3 Waveforms for Switching Energy Loss


Fig.3-1 Reverse Recovery Time Measurement Circuit


Fig.3-2 Reverse Recovery Waveform


## -Package Dimensions



Unit: mm


Unit: mm

## -Die Bonding Layout


-Front view of the packaging.
-Dimensions are design values.

- If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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